

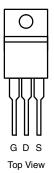
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COMPLIANT

N-Channel 250 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ)		
250	0.060 at V _{GS} = 10 V	40	95		
250	0.064 at V _{GS} = 6 V	38.7	95		





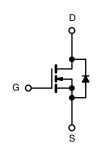
Ordering Information: SUP40N25-60-E3 (Lead (Pb)-free)



- TrenchFET[®] Power MOSFETS
- 175 °C Junction Temperature
- New Low Thermal Resistance Package
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

Industrial



N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	S ($T_C = 25 \degree C$, unless other	erwise noted)			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	250	- v	
Gate-Source Voltage		V _{GS}	± 30		
Continuous Drain Current (T _{.1} = 175 °C)	T _C = 25 °C	1-	40		
Continuous Drain Current $(1) = 175$ C)	T _C = 125 °C	I _D	23		
Pulsed Drain Current		I _{DM}	70	A	
Avalanche Current		I _{AR}	35		
Repetitive Avalanche Energy ^a	L = 0.1 mH	E _{AR}	61	mJ	
Maximum Dawar Dissinctional	T _C = 25 °C	Р	300 ^b		
Maximum Power Dissipation ^a	T _A = 25 °C ^c	– P _D	3.75	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W
Junction-to-Case (Drain)	R _{thJC}	0.5	0/11

Notes:

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR-4 material).

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Parameter	Symbol	Test Conditions	Min .	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 V$, $I_{D} = 250 \mu A$	250			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2		4	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 30 V$			± 250	nA
		$V_{DS} = 250 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			50	
		$V_{DS} = 250 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	70			Α
		V _{GS} = 10 V, I _D = 20 A		0.049	0.060	Ω
		V_{GS} = 10 V, I_{D} = 20 A, T_{J} = 125 °C			0.121	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V_{GS} = 10 V, I_{D} = 20 A, T_{J} = 175 °C			0.163	
		V _{GS} = 6 V, I _D = 15 A		0.051	0.064	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		70		S
Dynamic ^b					ļļ	
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		5000		pF
Output Capacitance	C _{oss}			300		
Reverse Transfer Capacitance	C _{rss}			170		
Total Gate Charge ^c	Qg			95	140	nC
Gate-Source Charge ^c	Q _{gs}	V _{DS} = 125 V, V _{GS} = 10 V, I _D = 45 A		28		
Gate-Drain Charge ^c	Q _{gd}			34		
Gate Resistance	R _g	f = 1 MHz		1.6		Ω
Turn-On Delay Time ^c	t _{d(on)}			22	35	
Rise Time ^c	tr	V_{DD} = 100 V, R _L = 2.78 Ω		220	330	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 45 \text{ A}, V_{GEN} = 10 \text{ V}, \text{ R}_g = 2.5 \Omega$		40	60	- ns
Fall Time ^c	t _f			145	220	
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C) ^b				
Continuous Current	ا _S				45	•
Pulsed Current	I _{SM}				70	A
Forward Voltage ^a	V _{SD}	I _F = 45 A, V _{GS} = 0 V		1	1.5	V
Reverse Recovery Time	t _{rr}			150	225	ns
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = 45 A, di/dt = 100 A/μs		12	18	Α
Reverse Recovery Charge	Q _{rr}			0.9	2	μC

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

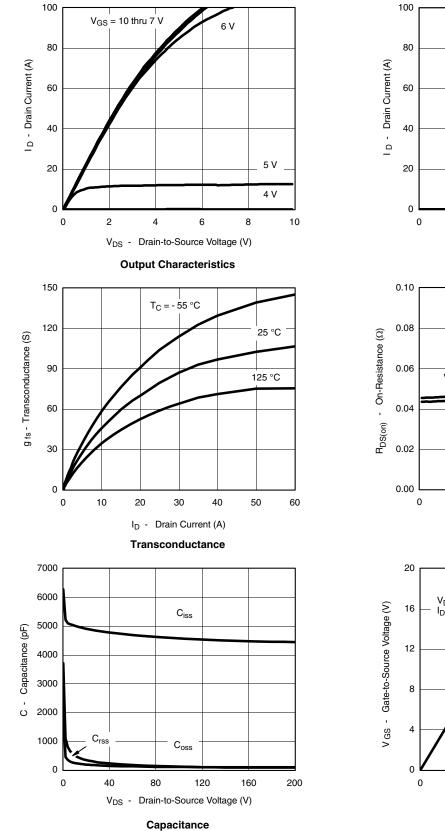
c. Independent of operating temperature.

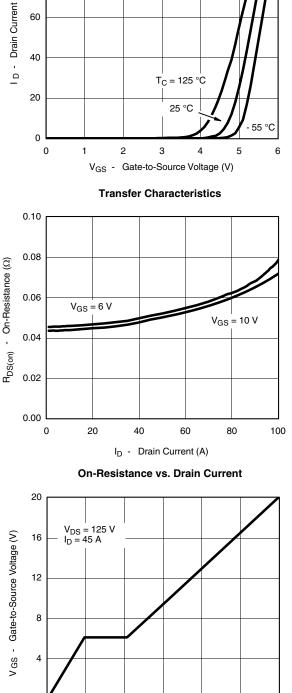
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Gate Charge

90

Qg - Total Gate Charge (nC)

120

150

30

60

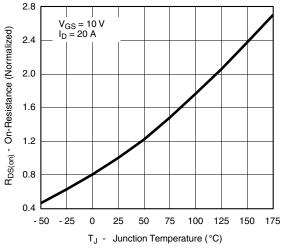
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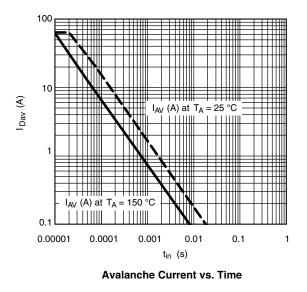
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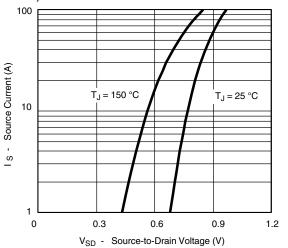
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



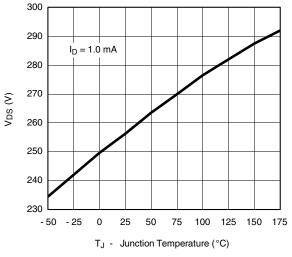
On-Resistance vs. Junction Temperature





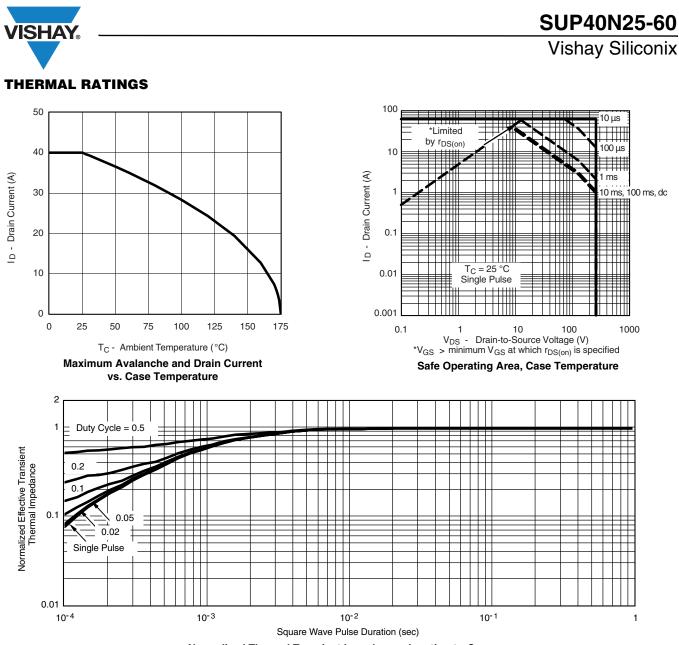
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Source-Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature

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Normalized Thermal Transient Impedance, Junction-to-Case

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TO-220AB



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
А	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
С	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
е	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
ØР	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
	0413-Rev. P,		0.102	0.118

Note

 * M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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